KMN1072KX5F 20V N-Channel Enhancement Mode MOSFET

Features

- 20V, 1A, $R_{DS(ON)}$=450mΩ@VGS=4.5V
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- ESD Protected
- SOT-323 package design

Product Description

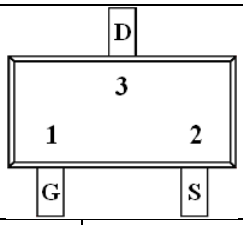
LMN1072 KX5F, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent RDS(ON), low gate charge. These devices are particularly suited for low voltage power management, such as smart phone and notebook computer, and low in-line power loss are needed in commercial industrial surface mount applications.

Applications

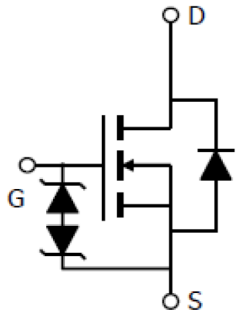
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Pagers

Pin Configuration

LMN1072 KX5F (SOT-323)



PIN	Description
1	Gate
2	Source
3	Drain



Notice: The information in this document is subject to change without notice.

Ordering Information

Ordering Information					
Part Number	P/N	PKG code	Pb Free code	Package	Quantity
LMN1072KX5F	LMN1072K	X5	F	SOT-323	3000 PCS

Marking Information

Marking Information		
Part Marking	Part Number	LFC code
2XWMM	2	XWMM

Absolute Maximum Ratings

(T_C=25ºC Unless otherwise noted)

Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		±10	V
I_D	Continuous Drain Current	T_A=25ºC	1	A
		T_A=70ºC	0.64	
I_{DM}	Pulsed Drain Current		4	A
P_D	Power Dissipation	T_A=25ºC	0.29	W
		T_A=70ºC	0.19	
T_J	Operating Junction Temperature		-55 to +150	℃
T_{STG}	Storage Temperature Range		-55 to +150	℃
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		425	℃/W

Notice: The information in this document is subject to change without notice.

Electrical Characteristics

(T_C=25ºC Unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	20			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, ID=250uA	0.3		1	
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±10V			±10	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V, V_{GS}=0V			1	uA
		V_{DS}=16V, V_{GS}=0V T_J=85℃			30	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=4.5V, ID=0.5A		220	450	mΩ
		V_{GS}=2.5V, ID=0.4A		280	600	
		V_{GS}=1.8V, ID=0.2A		390	750	
		V_{GS}=1.5V, ID=0.1A		540	1200	
V_{SD}	Diode Forward Voltage	I_S=0.15A, V_{GS}=0V			1.3	V
Dynamic						
Q_g	Total Gate Charge	V_{DS}=10V, V_{GS}=4.5V, I_D=0.25A		0.73		nC
Q_{gs}	Gate-Source Charge			0.93		
Q_{gd}	Gate-Drain Charge			0.12		
C_{iss}	Input Capacitance	V_{DS}=16V, V_{GS}=0V, f=1MHz		60.7		pF
C_{oss}	Output Capacitance			9.7		
C_{rss}	Reverse Transfer Capacitance			5.4		
$t_{d(on)}$	Turn-On Time	V_{DD}=10V, R_L=47Ω, I_D=0.2A, V_{GS}=4.5V, R_G=10Ω		5.1		ns
t_r				7.4		
$t_{d(off)}$	Turn-Off Time			26.7		
t_f				12.3		

Notice: The information in this document is subject to change without notice.

Typical Performance Characteristics

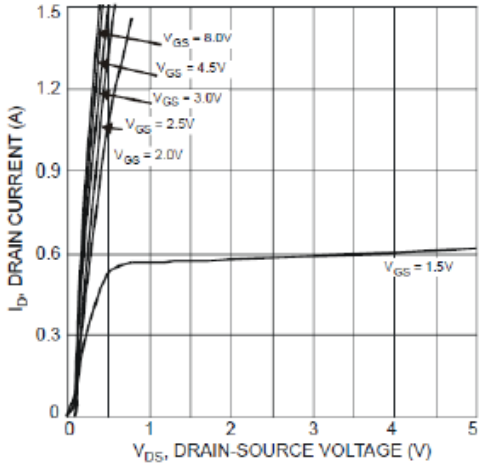


Fig. 1 Typical Output Characteristics

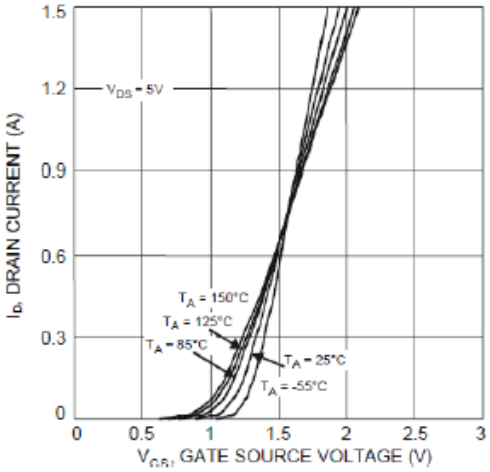


Fig. 2 Typical Transfer Characteristics

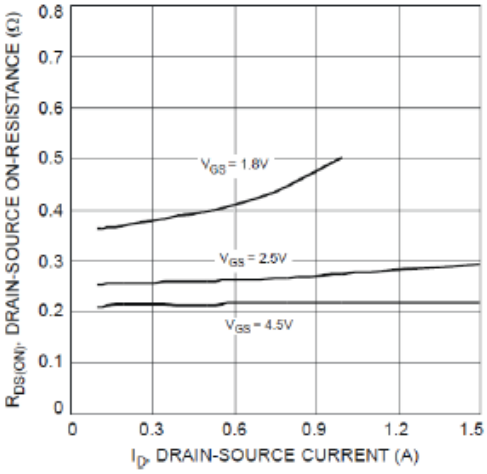


Fig. 3 Typical On-Resistance vs. I_D and V_{GS}

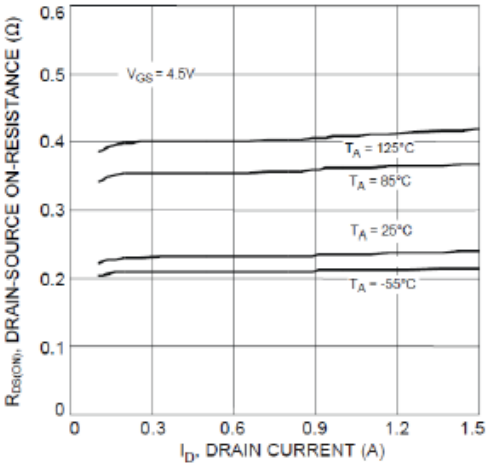


Fig. 4 Typical Drain-Source On-Resistance vs. I_D and T_J

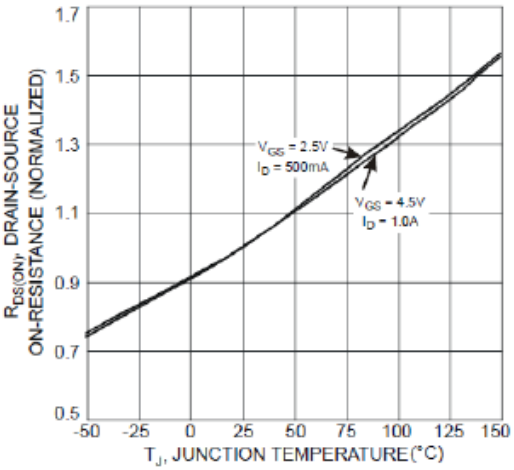


Fig. 5 On-Resistance Variation with T_J

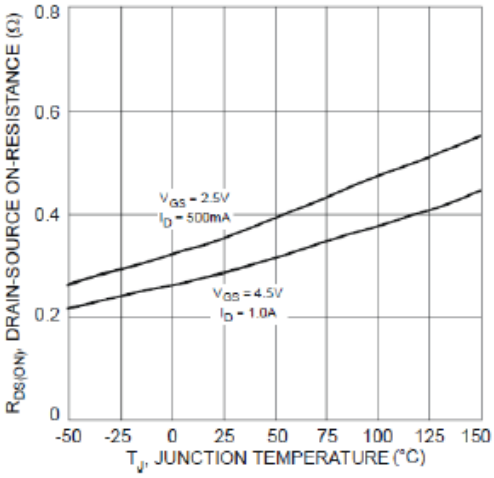


Fig. 6 On-Resistance Variation with T_J

Notice: The information in this document is subject to change without notice.

Typical Performance Characteristics(continue)

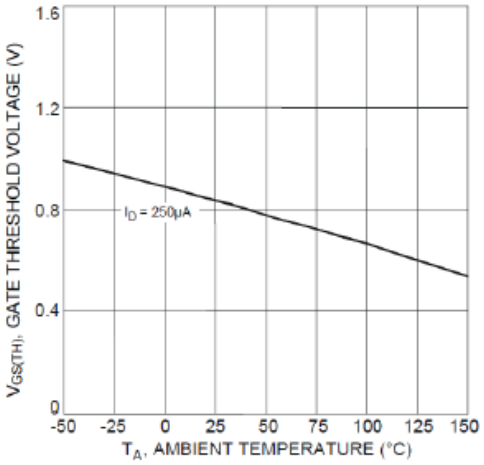


Fig. 7 Gate Threshold Variation vs. T_A

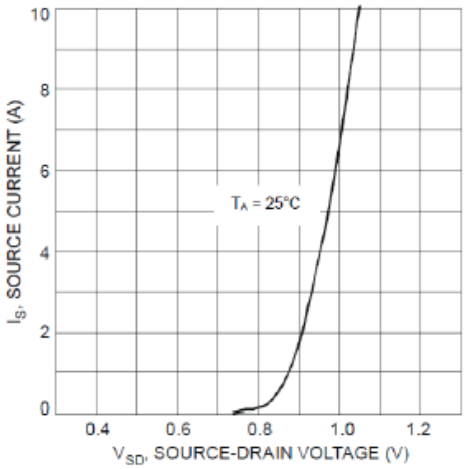


Fig. 8 Diode Forward Voltage vs. Current

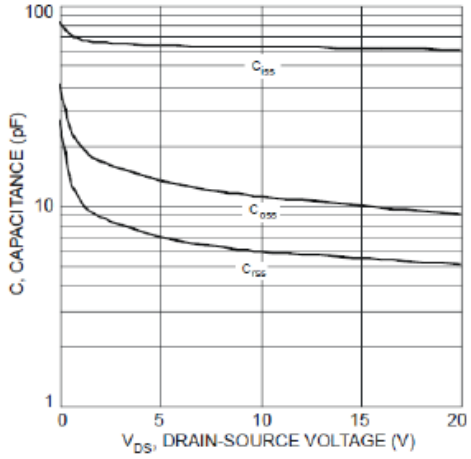


Fig. 9 Typical Capacitance

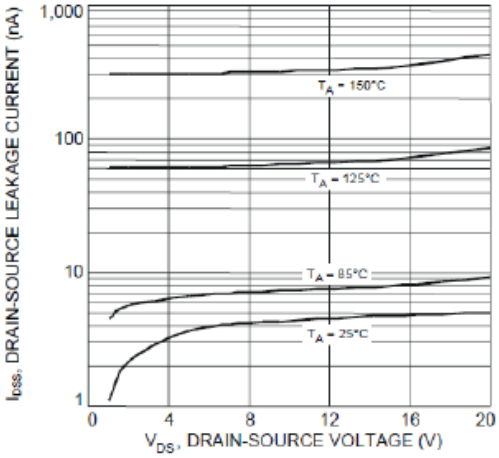


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

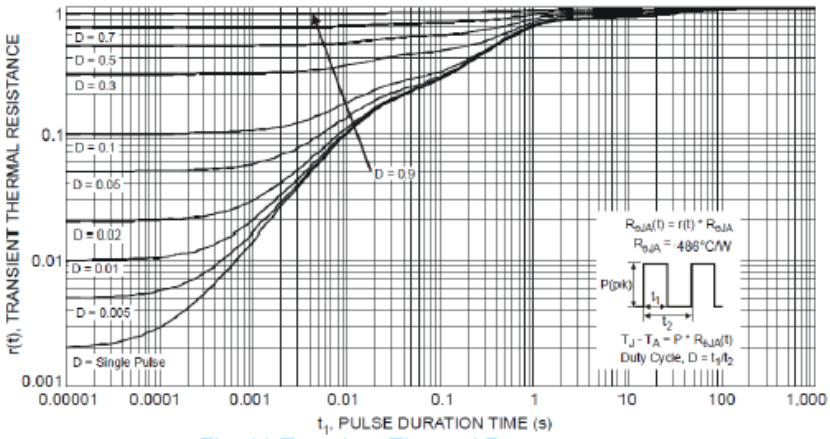


Fig. 11 Transient Thermal Response

Notice: The information in this document is subject to change without notice.

NOTICE:

LFC Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all LFC Semiconductor products described or contained herein. LFC Semiconductor products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. LFC Semiconductor makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Information furnished is believed to be accurate and reliable. However LFC Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of LFC Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of LFC Semiconductor.

Notice: The information in this document is subject to change without notice.